

Cat No.: Revision:

7-1S-2000-049 P1

AllnGaP LED DICE

PRELIMINARY

Part NO.: AOC-S20RxM-65 Series

Features

- Red color emission
- Excellent performance and high efficiency
- Great reliability even in harsh environment
- Mirror reflector to increase efficiency

Description

AOC-S20RxM-65 series is a red color emitting AlInGaP LED grown by MOCVD technique. Its structure enables enhanced quantum efficiency; the mirror reflector greatly increases the light extraction efficiency and therefore a greater light intensity. This device is designed for ultrahigh brightness (UHB) automobile, display, and consumer electronic applications.

Chip Dimensions



N-electrode					
EPI					
Substrate					
P-electrode					

Chip Size : $508\mu m \times 508\mu m \pm 25\mu m$ Bonding Pad : $\phi 106 \mu m \pm 10 \mu m$ Chip Thickness : $165\mu m \pm 25\mu m$

Electrical and Optics Characteristics

Measuring Item	Symbol	Condition	Min	Тур.	Max	Unit
Forward Voltage	\mathbf{V}_{F}	I _F =150mA	1.75	-	2.65	V
Reverse Current	Ir	V _R =5V	-	-	1.0	μA
Dominant Wavelength	λd	I _F =150mA	616	-	630	nm
Max. Junction Temperature	T _{max}	_	_	-	120	С°

Available Dominate Wavelength and Iv Matrix

Part No.	Wavelength Range	≥3000 mcd	≥3500 mcd	≥4000 mcd
S20RSM-65	616 ~ 625 nm	-	Y350	Y400
S20RMM-65	620 ~ 630 nm	Y300	Y350	Y400

Note:

All measurements are done with AOC's standard testing equipment.

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^{2.} Luminance intensity is measured on bare chip.

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Above contents are subject to change without notice. Special requests are also welcome, please contact AOC's sale representative for any request. Characteristics curves are measured within TO-46 package. 4.